

Investigation of the Physical Mechanism behind Retention Loss in FeFETs with MIFIFIS Gate Structure

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Abstract—A Metal-Gate Blocking Layer (GBL)-Ferroelectric-Tunnel Dielectric Layer (TDL)-Ferroelectric-Channel Insulator (Ch.IL)-Si (MIFIFIS) structure is proposed to achieve a larger MW for applications in Fe-NAND. However, the large retention loss (RL) in the MIFIFIS structure restricts its application. In this work, we vary the physical thickness of the GBL and TDL, and conduct an in-depth analysis of the energy bands of the gate structure to investigate the physical mechanism behind the RL in FeFETs with the MIFIFIS structure. The physical origin of the RL is that the electric field direction across the TDL reduces the potential barrier provided by the ferroelectric near the silicon substrate. Based on the above physical mechanism, the RL can be reduced to 12% and 0.2% by redesigning the gate structure or reducing the pulse amplitude, respectively. Our work contributes to a deeper understanding of the physical mechanism behind the RL in FeFETs with the MIFIFIS gate structure. It provides guidance for enhancing the reliability of FeFETs.

Index Terms—Ferroelectric, retention loss, $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$, MIFIFIS, FeFETs.

I. INTRODUCTION

SINCE the discovery of ferroelectricity in doped HfO_2 in 2011 [1], hafnia-based silicon channel ferroelectric field-effect transistors (HfO_2 Si-FeFETs) have attracted widespread research interest as a strong candidate for

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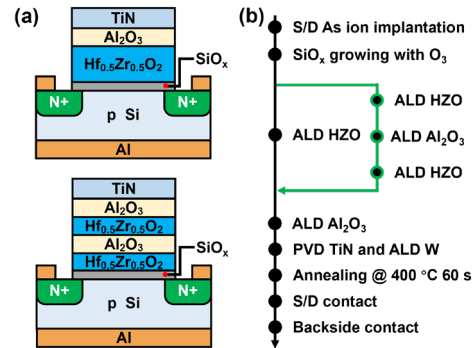


Fig. 1. (a) Schematic and (b) fabrication process flow of FeFETs.

nonvolatile memory with low write voltage, high switching speed, CMOS compatibility, and excellent scalability [2-17]. For FeFETs with the MFIS gate structure, the large amount of charge injected from the silicon channel shields the spontaneous polarization of the ferroelectric [18-21]. This results in a narrow memory window (MW), and the MW is generally limited to less than 2 V [22-25], which severely restricts its application in multi-bit memory.

Recently, a Metal-Gate Blocking Layer (GBL)-Ferroelectric-Tunnel Dielectric Layer (TDL)-Ferroelectric-Channel Insulator (Ch.IL)-Si (MIFIFIS) structure has been proposed to achieve a larger MW [26-28]. Unfortunately, the retention characteristics of the MIFIFIS gate structure exhibit a significant degradation. The retention loss (RL) exceeds 25%, which limits its application in Fe-NAND [29, 30]. Therefore, we conducted a detailed study on the physical mechanism behind the RL in the MIFIFIS gate structure. This mechanism is attributed to the direction of the electric field across TDL pointing towards the silicon substrate, which reduces the potential barrier provided by the ferroelectric near the silicon substrate.

In addition, to reverse the electric field direction across the TDL (specifically, directing it toward the silicon substrate), we propose the following strategies: (i) inserting a charge-trapping layer (CTL) on both sides of the TDL to increase the charge density at the TDL ends, or (ii) reducing the operating voltage amplitude to decrease the charge density at the GBL/FE interface. Using these methods, the RL can be reduced to 12% and 0.2%, respectively. This study provides guidance for improving FeFET reliability through gate stack engineering

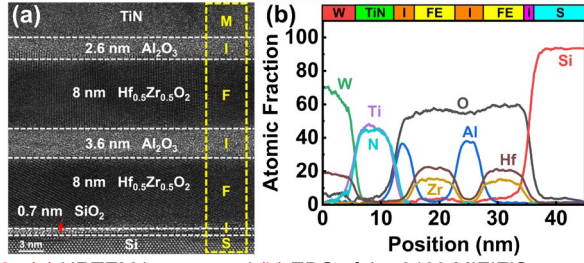


Fig. 2. (a) HRTEM images and (b) EDS of the 8483 MIFIFIS structure.

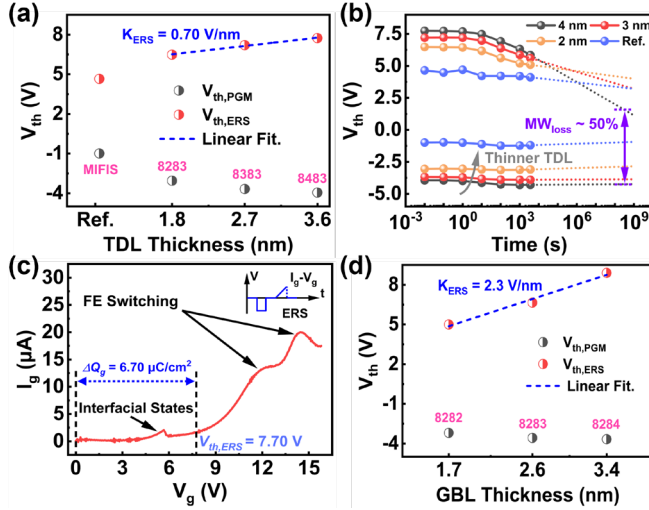


Fig. 3. The measurement results of (a) V_{th} and (b) retention characteristics corresponding to the maximum MW. (c) The I_g - V_g curve of the reading process after the erase pulse. (d) The dependence of V_{th} corresponding to the maximum MW on the physical thickness of the GBL.

and optimizing pulse conditions.

II. DEVICE FABRICATION AND CHARACTERIZATION

We fabricated FeFETs with different gate structures, as shown in Fig. 1(a). One is a TiN/ Al_2O_3 / $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ / SiO_x /Si (MIFIS) structure with 18 nm $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ and 3 nm Al_2O_3 as the control sample, and the other is a TiN/ Al_2O_3 / $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ / Al_2O_3 / $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ / SiO_x /Si (MIFIFIS) structure with 8 nm $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$. For the MIFIFIS structure, when the TDL thickness is 2 nm, the GBL thickness is 2-, 3-, or 4 nm, and when the GBL thickness is 3 nm, the TDL thickness is 2-, 3-, or 4 nm. For simplicity, we denote the gate stacks by their ferroelectric/TDL/ferroelectric/GBL nominal thicknesses. For example, 8/2/8/2 (8282), 8/2/8/3 (8283), and 8/2/8/4 (8284). Fig. 1(b) shows the fabrication process flow. This detailed process flow is described in our previous works [31, 32]. All of the fabrication processes of the MIFIS structure are the same as the MIFIFIS structure, except that the gate structure and thickness of the dielectric layer are different.

Fig. 2 shows the High-Resolution Transmission Electron Microscopy (HRTEM) images and the Energy Dispersion Spectrometer (EDS) of the 8483 MIFIFIS structure.

In this work, the gate length/width (L/W) of the FeFETs is 5/150 μm . The electrical measurements were performed by Keysight B1500A. The threshold voltage (V_{th}) is extracted by the constant current method.

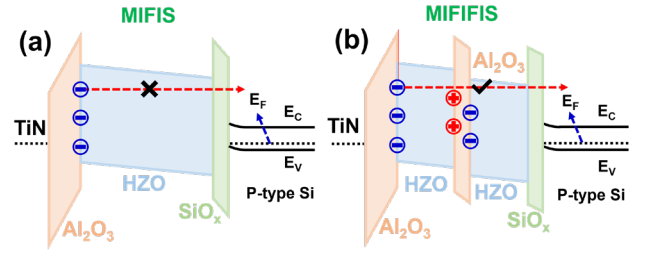


Fig. 4. The energy band diagram of (a) the MIFIS structure and (b) the 8283 MIFIFIS structure after the erase operation.

III. RESULTS AND DISCUSSION

We first study the maximum MW of the FeFETs with different gate structures. Here, we find the maximum MW by adopting different program/erase (P/E) voltage amplitudes under the pulse width of 50 μs for each sample. Fig. 3(a) shows the dependence of V_{th} , which corresponds to the maximum MW, on the TDL thickness. For the MIFIS structure and the 8283 MIFIFIS structure, at the same physical thickness of the gate stack, the 8283 MIFIFIS structure shows a maximum MW of 9.5 V, while the MIFIS gate structure shows a maximum MW of 5.7 V. Therefore, inserting an Al_2O_3 interlayer in the middle of the ferroelectric $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ can increase the MW of FeFETs, which is consistent with the phenomenon reported in [33, 34]. This is attributed to the presence of the trapped charges at both ends of the TDL [7, 33]. Furthermore, we find that $V_{th,ERS}$ increases linearly with the increase of the TDL thickness. According to (1), this slope K_{ERS} in Fig. 3(a) represents the magnitude of the electric field across the TDL at $V_g = V_{th,ERS}$.

$$V_{th} = \varphi_{MS} + 2\varphi_B + \frac{1}{C_{TDL}} \cdot (Q_{TDL} + Q_{t_Ch} + Q_{Si_th}) + \frac{1}{C_{GBL}} \cdot (Q_{t_GBL} + Q_{t_Ch} + Q_{Si_th}) + \frac{2}{C_{FE}} \cdot (P_{FE_th} + Q_{t_Ch} + Q_{Si_th}) + \frac{1}{C_{BIL}} \cdot Q_{Si_th} \quad (1)$$

Here, Q_{t_Ch} , Q_{t_TDL} , Q_{t_GBL} , and Q_{Si_th} respectively represent the charge densities at the GBL/FE, TDL/FE, FE/Ch.IL interfaces, and on the silicon substrate when $V_g = V_{th}$.

We investigate the retention characteristics under the maximum MW. Fig. 3(b) shows the measurement results of retention characteristics. We find that the retention characteristics of the MIFIFIS structure have significantly degraded compared to the MIFIS structure, and the RL increases with the increase of the TDL thickness. In addition, we find that the RL is mainly caused by the rapid degradation of the $V_{th,ERS}$. Therefore, we need to investigate the physical origin of the $V_{th,ERS}$ degradation when $V_g = 0$ V after the erase operation. The latest research results indicate that the de-trapping of the trapped charges at the GBL/FE onto the silicon substrate leads to the RL of the $V_{th,ERS}$ in the MIFIS gate structure [35, 36]. Thus, we investigate the effect of the TDL insertion and increased TDL thickness on the de-trapping potential barrier of the trapped charges.

We discuss in detail the effect of the TDL insertion on the de-trapping potential barrier through an in-depth analysis of the energy bands. We measure the same I_g - V_g curve as the reading process after the erase operation. Fig. 3(c) shows the

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